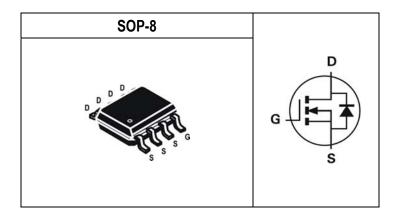


40V N-Channel Power MOSFET

Parameter	Value	Unit
V_{DSS}	40	V
R _{DS(ON)} max. V _{GS} =10V	14.5	mΩ
RDS(ON) max. VGS=4.5V	22	mΩ
l _D	10	Α



Features	Application
 Low On-Resistance Low Input Capacitance Low Miller Charge Low Input / Output Leakage Pb-free lead plating; RoHS compliant 	 Motor / Body Load Control Automotive Systems Load Switch DC-DC converters and Off-line UPS

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG40N04S	Halogen-Free	SOP-8	S	Tape & Reel	3,000

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parame	eter	Symbol	Value	Unit
Drain-Source Voltage		V _{DS}	40	V
Gate-Source Voltage		V _{GS}	±20	V
Drain Current-Continuous	T _A =25°C	I-	10	А
Drain Current-Continuous	T _A =70°C	ID	8	А
Drain Current-Pulsed Note 1		I _{DM}	35	А
Avalanche Current		I _{AS}	25	А
Avalanche Energy, L=0.1mH		Eas	31	mJ
Maximum Dower Dissipation	T _C =25°C	PD	1.7	W
Maximum Power Dissipation	T _C =70°C	FD FD	0.7	W
Storage Temperature Range		T _{STG}	-55 to +150	°C
Operating Junction Temperature Range		TJ	-55 to +150	°C

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient	$R_{\theta JA}$	Steady State	-	-	75	°C/W
Maximum Junction-to-Case	Rejc	Steady State	-	-	24	°C/W

1



40V N-Channel Power MOSFET

Electrical Characteristics (T_J=25°C unless otherwise noted)

OFF CHARACTERISTICS							
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =250µA	40	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	μΑ	
Gate-Body Leakage	Igss	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA	

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =250µA	1	-	2.5	V
Drain-Source On-State Resistance	В	V _{GS} =10V, I _{DS} =8A	-	13.5	14.5	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _{DS} =5A	-	18.5	22	mΩ
Forward Transconductance Note 1	g fs	V _{DS} =5V, I _D =8A	-	35	-	S

DYNAMIC CHARACTERISTICS							
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Input Capacitance	C _{iss}		-	1248	-		
Output Capacitance	Coss	V _{DS} =20V, V _{GS} =0V, f=1MHz	-	114	-	pF	
Reverse Transfer Capacitance	Crss		-	84	-		
Gate Resistance	Rg	V _{GS} =0V, V _{DS} =0V, f=1MHz	-	2	-	Ω	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T _{d(on)}		-	8.17	-	
Rise Time	tr	V _{DD} =20V, I _D =8A, V _{GS} =10V,	-	3.23	-	
Turn-Off Delay Time	T _{d(off)}	Rg=3.3Ω	-	23.75	-	ns
Fall Time	t _f		-	2.09	-	
Total Gate Charge	Qg		-	10.16	-	
Gate to Source Gate Charge	Q _{gs}	V _{DS} =20V, I _{DS} =8A, V _{GS} =4.5V	-	3.13	-	nC
Gate to Drain "Miller" Charge	Q _{gd}		-	3.99	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
Parameter Symbol Conditions Min. Typ. Max. Unit					Unit		
Maximum Body-Diode Continuous Current	Is	V _G =V _D =0V, Force Current	-	-	38	Α	
Pulsed Source Current	I _{SM}	V _G =V _D =0V, Force Current	-	-	100	Α	
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =8A	-	-	1.2	V	

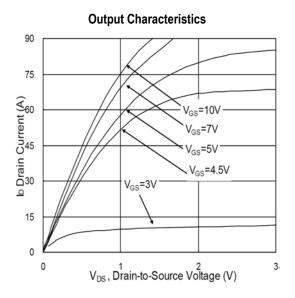
Notes:

- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 2. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Rejuc is guaranteed by design while Rejah is determined by the user's board design. Rejah shown below for single device operation on FR-4 in still air.

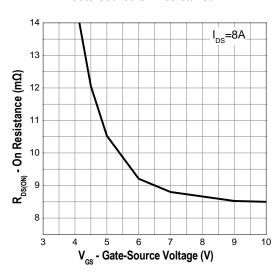


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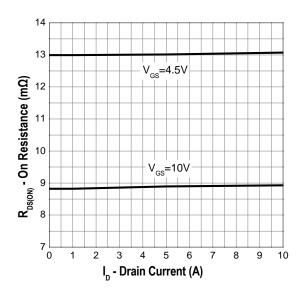
Typical Operating Characteristics



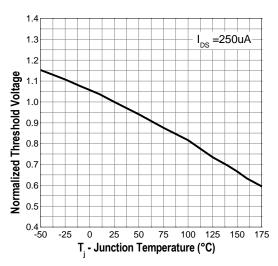
Gate-Source On Resistance



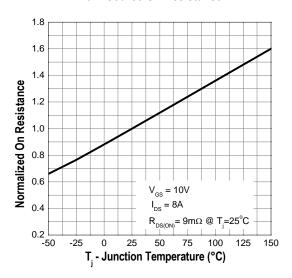
Drain-Source On Resistance



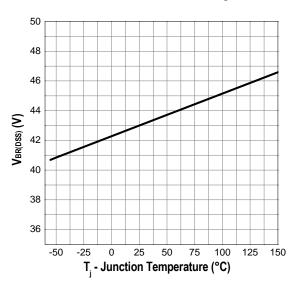
Gate Threshold Voltage



Drain-Source On Resistance



Drain-source Breakdown Voltage

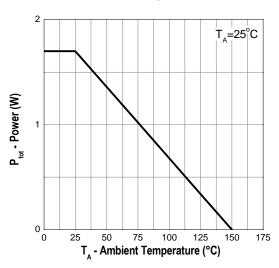




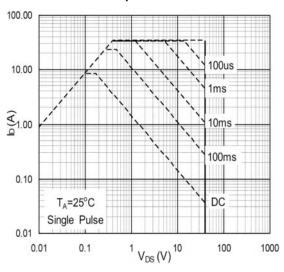
40V N-Channel Power MOSFET

Typical Operating Characteristics (Cont.)

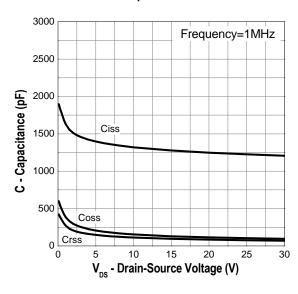
Power Dissipation



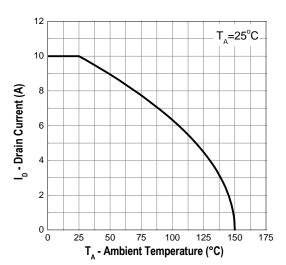
Safe Operation Area



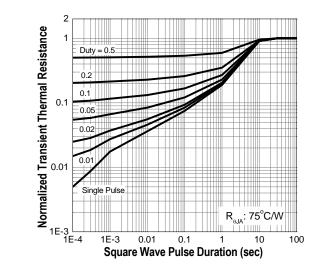
Capacitance



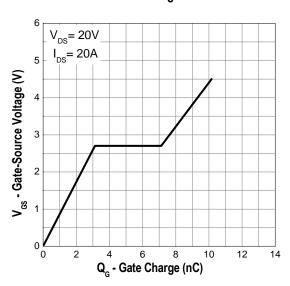
Drain Current



Transient Thermal Impedance



Gate Charge





SG40N04S
40V N-Channel Power MOSFET

Marking Information

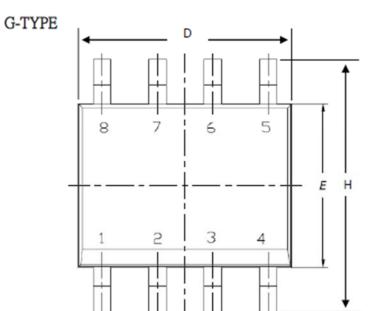
SOP-8	Marking Rule
Laser Marking	Line 1 : Device Name
	SG40N04S
	Line 2 : Date Code
SG40N04S	YYMMXXX
YYMMXXX	YY: Year Code
	MM: Month Code
	XXX: Serial Number



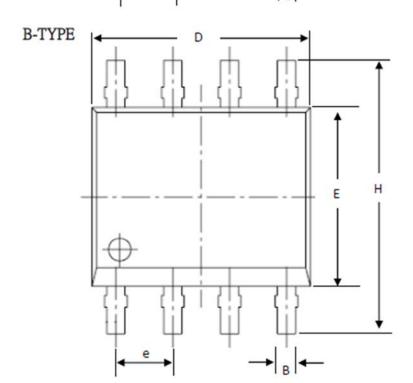


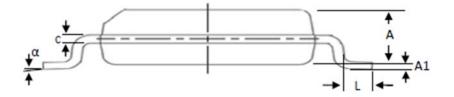
40V N-Channel Power MOSFET

Package of Dimension



Symbol	Min	Nor	Max
Α	1.35	1.55	1.75
A1	0.10	0.18	0.25
В	0.31	0.41	0.51
С	0.17	0.21	0.25
D	4.80	4.90	5.00
E	3.80	3.90	4.00
e	1.27	1.27	1.27
Н	5.80	6.00	6.20
L	0.40	0.84	1.27
α	0.00	4.00	8.00



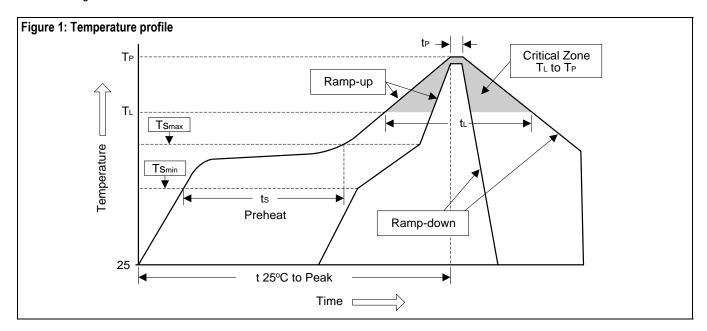




40V N-Channel Power MOSFET

Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts _{min})	100°C	150°C
- Temperature Max (Ts _{max})	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T∟)	183°C	217°C
- Time (t∟)	60 to 150 sec	60 to 150 sec
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec
Temperature (t₂)		
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



40V N-Channel Power MOSFET

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